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FIG 1: Power dissipation vs. on-state current

(per thyristor or diode)

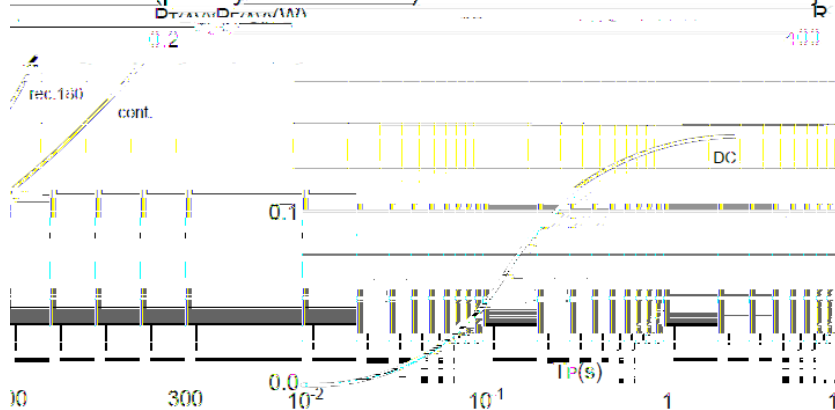


FIG 2: Maximum transient thermal impedance

junction to case (per thyristor or diode)

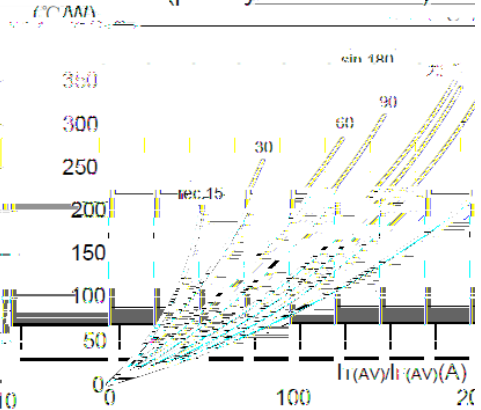


FIG 3: Forward resistance

(per thyristor or diode)

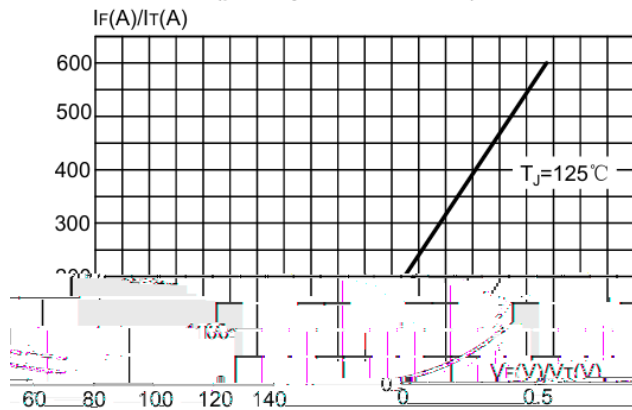


FIG 4: Relative positions of gate trigger current and latching current

current and latching current versus junction temperature

$I_{GT}, I_H, I_L(T_j)/I_{GT}, I_H, I_L(T_j=25^\circ\text{C})$

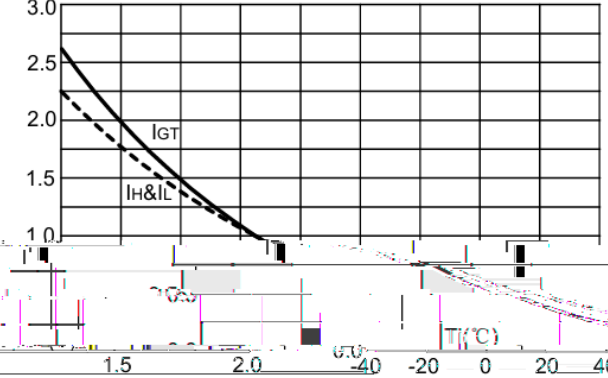


FIG 5: Gate trigger characteristics



FIG 6: Forward current vs. case temperature

